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[ON Semiconductor](#)
[NSS12100M3T5G](#)

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NSS12100M3T5G

12 V, 1 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical application are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

Features

- High Continuous Current Capability (1 A)
- Low $V_{CE(sat)}$ (150 mV Typical @ 500 mA)
- Small Size 1.2 mm x 1.2 mm
- This is a Pb-Free Device

Benefits

- High Specific Current and Power Capability Reduces Required PCB Area
- Reduced Parasitic Losses Increases Battery Life

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	-12	Vdc
Collector-Base Voltage	V_{CBO}	-12	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current - Continuous	I_C	-1.0	Adc
- Peak	I_{CM}	-3.0	
Electrostatic Discharge	ESD	HBM Class 3B MM Class C	

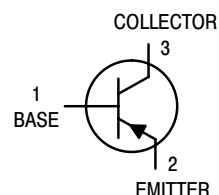
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



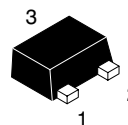
ON Semiconductor[®]

<http://onsemi.com>

12 VOLTS, 1.0 AMPS
PNP LOW $V_{CE(sat)}$ TRANSISTOR
EQUIVALENT $R_{DS(on)}$ 350 m Ω



MARKING DIAGRAM



SOT-723
CASE 631AA
STYLE 1



VE = Specific Device Code
 M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NSS12100M3T5G	SOT-723 (Pb-Free)	8000/ Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 1)	460 3.7	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 1)	270	$^\circ\text{C/W}$
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 2)	625 5.0	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 2)	200	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Lead 3	$R_{\theta JL}$	105	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector - Emitter Breakdown Voltage, ($I_C = -10 \text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	-12	-	-	Vdc
Collector - Base Breakdown Voltage, ($I_C = -0.1 \text{ mAdc}, I_E = 0$)	$V_{(BR)CBO}$	-12	-	-	Vdc
Emitter - Base Breakdown Voltage, ($I_E = -0.1 \text{ mAdc}, I_C = 0$)	$V_{(BR)EBO}$	-5.0	-	-	Vdc
Collector Cutoff Current, ($V_{CB} = -12 \text{ Vdc}, I_E = 0$)	I_{CBO}	-	-0.01	-0.1	μAdc
Emitter Cutoff Current, ($V_{CES} = -5.0 \text{ Vdc}, I_E = 0$)	I_{EBO}	-	-0.01	-0.1	μAdc

ON CHARACTERISTICS

DC Current Gain (Note 3) ($I_C = -10 \text{ mA}, V_{CE} = -2.0 \text{ V}$) ($I_C = -500 \text{ mA}, V_{CE} = -2.0 \text{ V}$) ($I_C = -1.0 \text{ A}, V_{CE} = -2.0 \text{ V}$)	h_{FE}	200 120 80	- - -	- - -	
Collector - Emitter Saturation Voltage (Note 3) ($I_C = -0.05 \text{ A}, I_B = -0.005 \text{ A}$) (Note 4) ($I_C = -0.1 \text{ A}, I_B = -0.002 \text{ A}$) ($I_C = -0.1 \text{ A}, I_B = -0.010 \text{ A}$) ($I_C = -0.5 \text{ A}, I_B = -0.050 \text{ A}$) ($I_C = -1.0 \text{ A}, I_B = -0.100 \text{ A}$)	$V_{CE(sat)}$	- - - - -	-0.030 -0.060 -0.040 -0.155 -0.350	-0.035 -0.080 -0.060 -0.220 -0.410	V
Base - Emitter Saturation Voltage (Note 3) ($I_C = -1.0 \text{ A}, I_B = -0.01 \text{ A}$)	$V_{BE(sat)}$	-	0.95	-1.15	V
Base - Emitter Turn-on Voltage (Note 3) ($I_C = -2.0 \text{ A}, V_{CE} = -2.0 \text{ V}$)	$V_{BE(on)}$	-	-1.05	-1.15	V

SMALL-SIGNAL CHARACTERISTICS

Input Capacitance ($V_{EB} = -0.5 \text{ V}, f = 1.0 \text{ MHz}$)	C_{ibo}	-	40	50	pF
Output Capacitance ($V_{CB} = -3.0 \text{ V}, f = 1.0 \text{ MHz}$)	C_{obo}	-	15	20	pF
Noise Figure ($I_C = 0.2 \text{ mA}, V_{CE} = 5.0 \text{ V}, R_S = 1.0 \text{ k}\Omega, f = 1.0 \text{ MHz}, BW = 200 \text{ Hz}$)	NF	-	-	5.0	dB

1. FR-4 @ 100 mm^2 , 1 oz copper traces.
2. FR-4 @ 500 mm^2 , 1 oz copper traces.
3. Pulsed Condition: Pulse Width = 300 μsec , Duty Cycle $\leq 2\%$.
4. Guaranteed by design but not tested.

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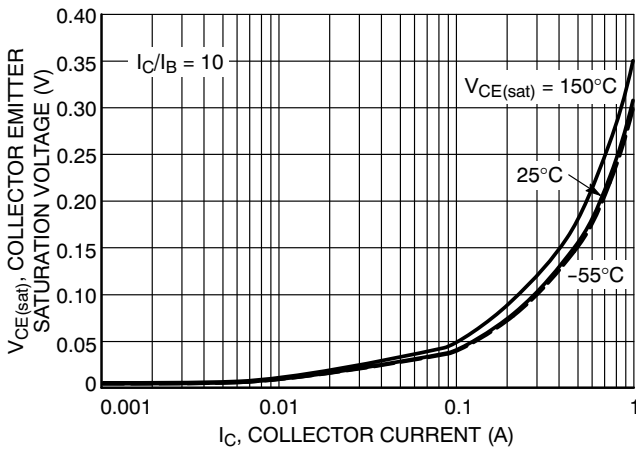


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

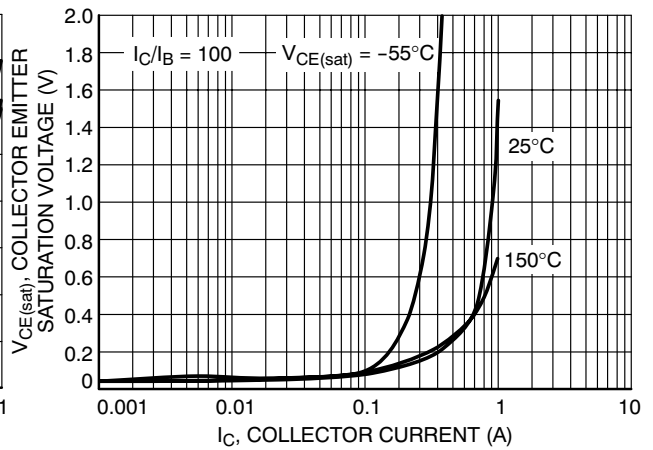


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

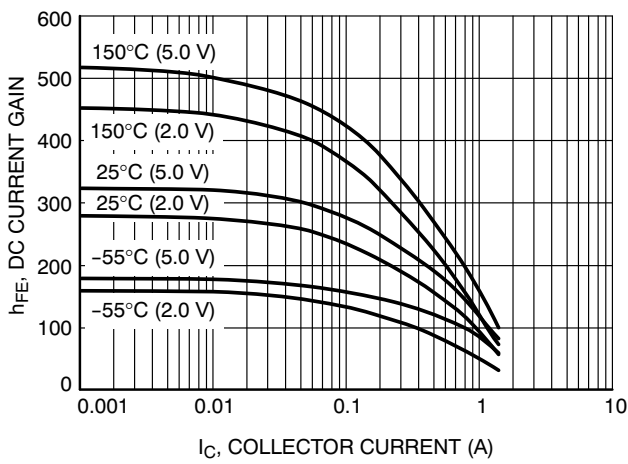


Figure 3. DC Current Gain vs. Collector Current

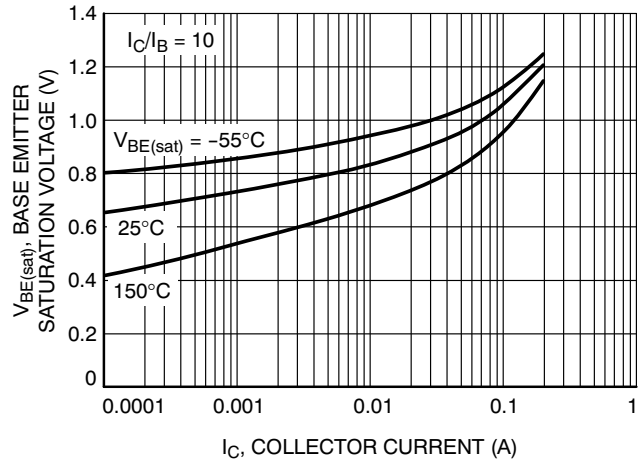


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

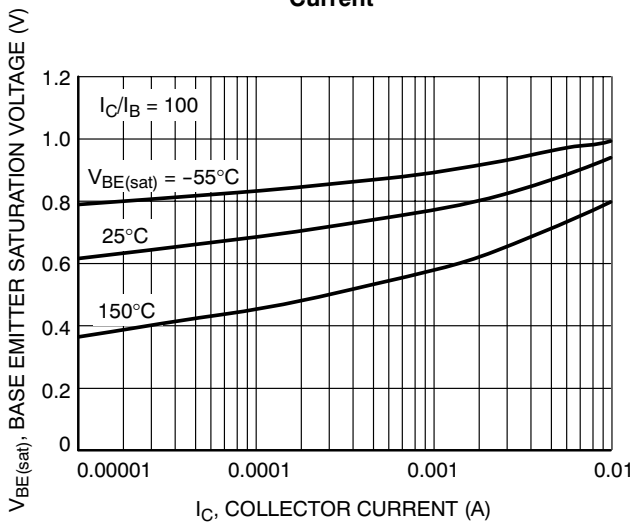


Figure 5. Base Emitter Saturation Voltage vs. Collector Current

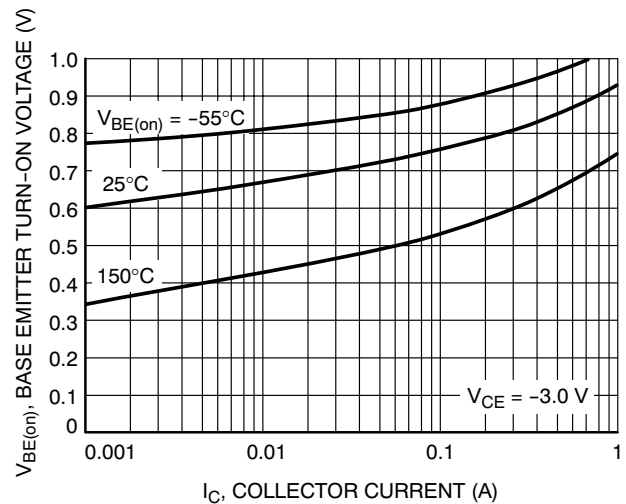


Figure 6. Base Emitter Turn-On Voltage vs. Collector Current

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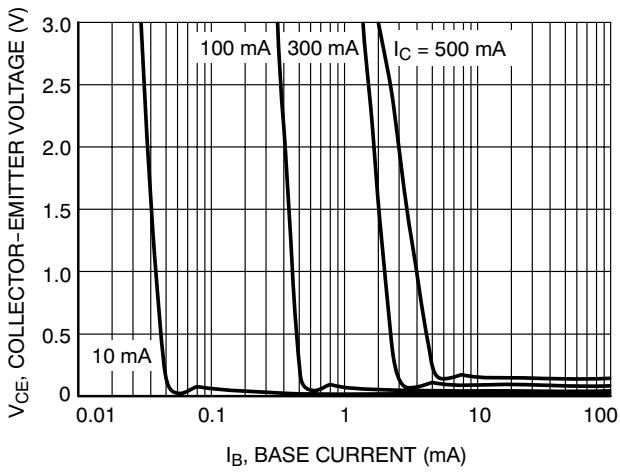


Figure 7. Saturation Region @ 25°C

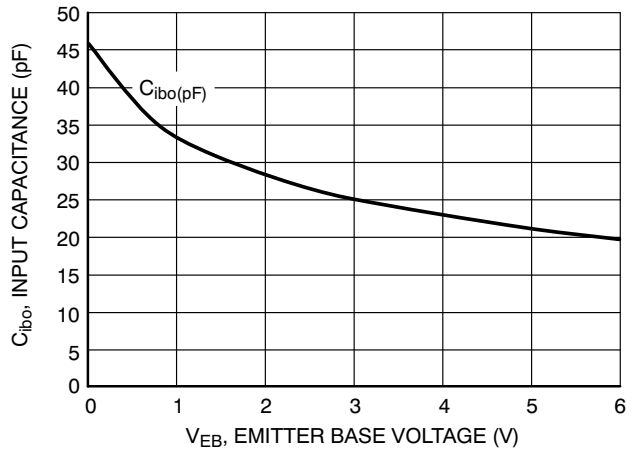


Figure 8. Input Capacitance

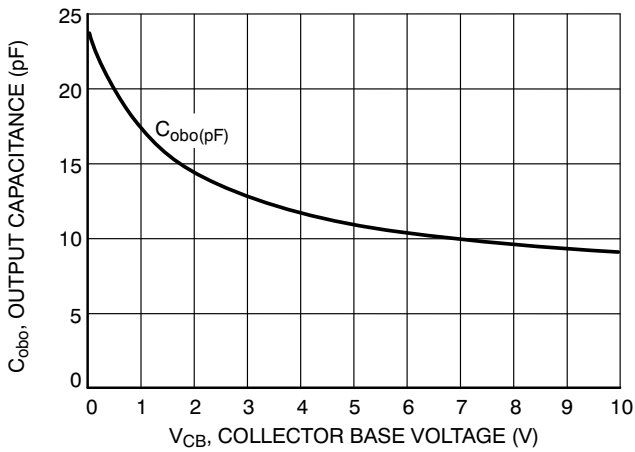


Figure 9. Output Capacitance

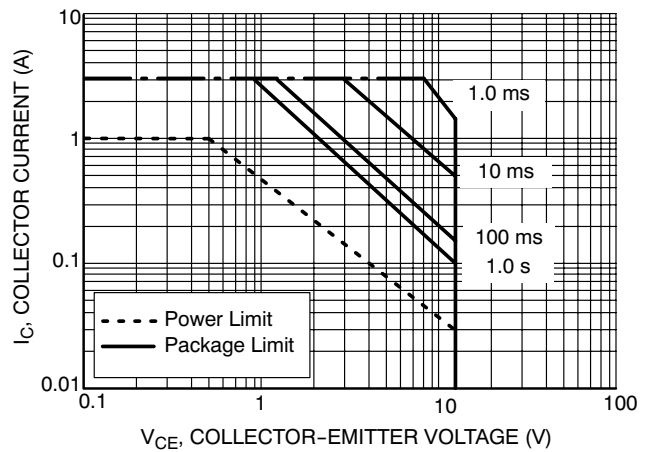
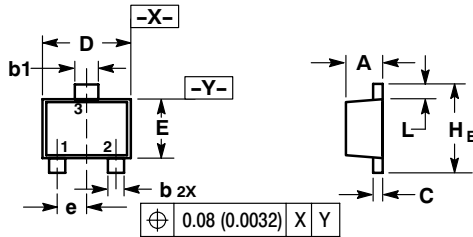


Figure 10. Safe Operating Area

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PACKAGE DIMENSIONS

SOT-723
CASE 631AA-01
ISSUE C



NOTES:

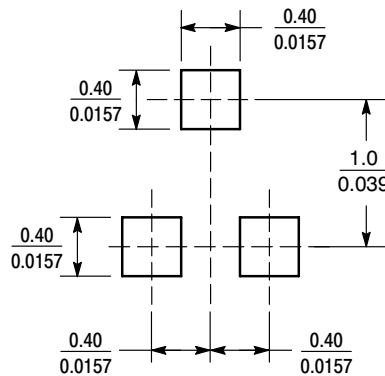
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
b	0.15	0.21	0.27	0.0059	0.0083	0.0106
b1	0.25	0.31	0.37	0.010	0.012	0.015
C	0.07	0.12	0.17	0.0028	0.0047	0.0067
D	1.15	1.20	1.25	0.045	0.047	0.049
E	0.75	0.80	0.85	0.03	0.032	0.034
e	0.40 BSC			0.016 BSC		
H E	1.15	1.20	1.25	0.045	0.047	0.049
L	0.15	0.20	0.25	0.0059	0.0079	0.0098

STYLE 1:

- PIN 1. BASE
- EMITTER
- COLLECTOR

SOLDERING FOOTPRINT*



SCALE 20:1 (mm/inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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